



P-Channel Enhancement-Mode Vertical DMOS FETs

Ordering Information

BV _{DSS} / BV _{DGS}	R _{DS(ON)} (max)	I _{D(ON)} (min)	V _{GS(th)} (max)	Order Number / Package
				TO-92
-200V	12Ω	-0.75A	-2.4V	TP0620N3

† MIL visual screening available

Features

- Low threshold — -2.4 V max
- High input impedance
- Low input capacitance — 85pF typical
- Fast switching speeds
- Low on resistance
- Free from secondary breakdown
- Low input and output leakage
- Complementary N- and P-channel devices

Low Threshold DMOS Technology

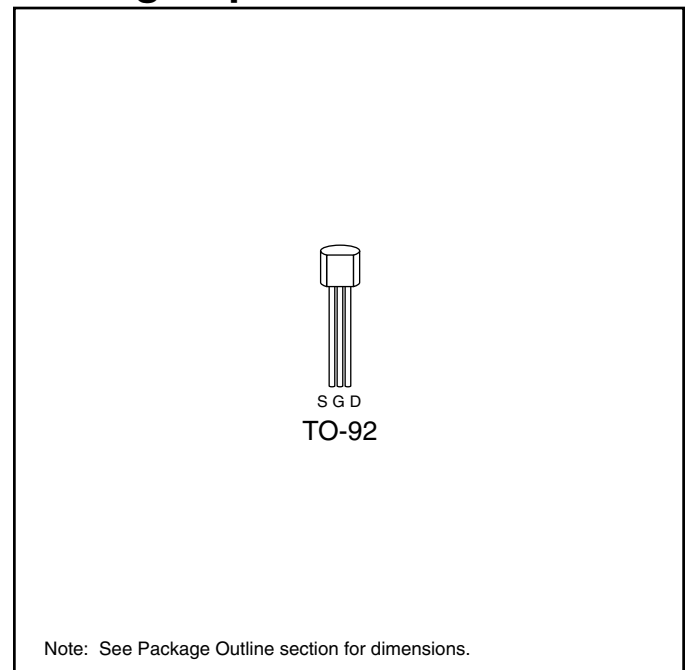
These low threshold enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Applications

- Logic level interfaces – ideal for TTL and CMOS
- Solid state relays
- Battery operated systems
- Photo voltaic drives
- Analog switches
- General purpose line drivers
- Telecom switches

Package Option



Absolute Maximum Ratings

Drain-to-Source Voltage	BV _{DSS}
Drain-to-Gate Voltage	BV _{DGS}
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

* Distance of 1.6 mm from case for 10 seconds.

11/12/01

Supertex Inc. does not recommend the use of its products in life support applications and will not knowingly sell its products for use in such applications unless it receives an adequate "products liability indemnification insurance agreement." Supertex does not assume responsibility for use of devices described and limits its liability to the replacement of devices determined to be defective due to workmanship. No responsibility is assumed for possible omissions or inaccuracies. Circuitry and specifications are subject to change without notice. For the latest product specifications, refer to the Supertex website: <http://www.supertex.com>. For complete liability information on all Supertex products, refer to the most current databook or to the Legal/Disclaimer page on the Supertex website.

Thermal Characteristics

Package	I_D (continuous)*	I_D (pulsed)	Power Dissipation @ $T_C = 25^\circ\text{C}$	θ_{jc} $^\circ\text{C/W}$	θ_{ja} $^\circ\text{C/W}$	I_{DR}^*	I_{DRM}
TO-92	-175mA	-0.8A	1W	125	170	-175mA	-0.8A

* I_D (continuous) is limited by max rated T_j .

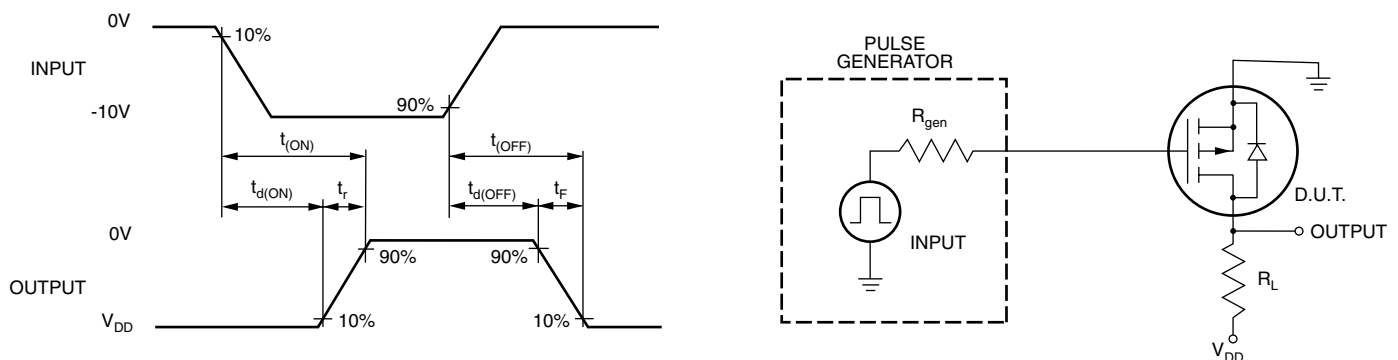
Electrical Characteristics (@ 25°C unless otherwise specified)

Symbol	Parameter	Min	Typ	Max	Unit	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	-200			V	$V_{GS} = 0V, I_D = -2.0mA$
$V_{GS(th)}$	Gate Threshold Voltage	-1.0		-2.4	V	$V_{GS} = V_{DS}, I_D = -1.0mA$
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature			-4.5	mV/ $^\circ\text{C}$	$V_{GS} = V_{DS}, I_D = -1.0mA$
I_{GSS}	Gate Body Leakage			-100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
I_{DSS}	Zero Gate Voltage Drain Current			-10	μA	$V_{GS} = 0V, V_{DS} = \text{Max Rating}$
				-1.0	mA	$V_{GS} = 0V, V_{DS} = 0.8 \text{ Max Rating}$ $T_A = 125^\circ\text{C}$
$I_{D(ON)}$	ON-State Drain Current	-0.25			A	$V_{GS} = -5V, V_{DS} = -25V$
		-0.75				$V_{GS} = -10V, V_{DS} = -25V$
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance		9.0	15	Ω	$V_{GS} = -5V, I_D = -0.1A$
			7.0	12		$V_{GS} = -10V, I_D = -0.2A$
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature			1.7	%/ $^\circ\text{C}$	$V_{GS} = -10V, I_D = -0.2A$
G_{FS}	Forward Transconductance	100	150		m Ω	$V_{DS} = -25V, I_D = -0.4A$
C_{ISS}	Input Capacitance		85	150	pF	$V_{GS} = 0V, V_{DS} = -25V$ $f = 1 \text{ MHz}$
C_{OSS}	Common Source Output Capacitance		30	85		
C_{RSS}	Reverse Transfer Capacitance		10	35		
$t_{d(ON)}$	Turn-ON Delay Time			10	ns	$V_{DD} = -25V$ $I_D = -0.75A$ $R_{GEN} = 25\Omega$
t_r	Rise Time			15		
$t_{d(OFF)}$	Turn-OFF Delay Time			20		
t_f	Fall Time			16		
V_{SD}	Diode Forward Voltage Drop			-1.8	V	$V_{GS} = 0V, I_{SD} = -0.5A$
t_{rr}	Reverse Recovery Time		300		ns	$V_{GS} = 0V, I_{SD} = -0.5A$

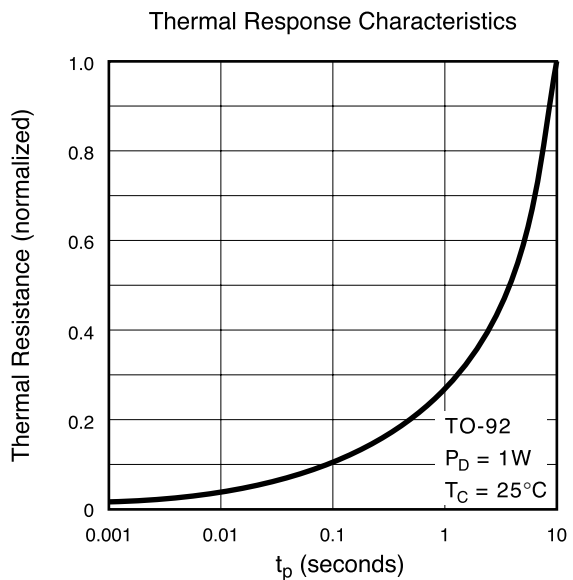
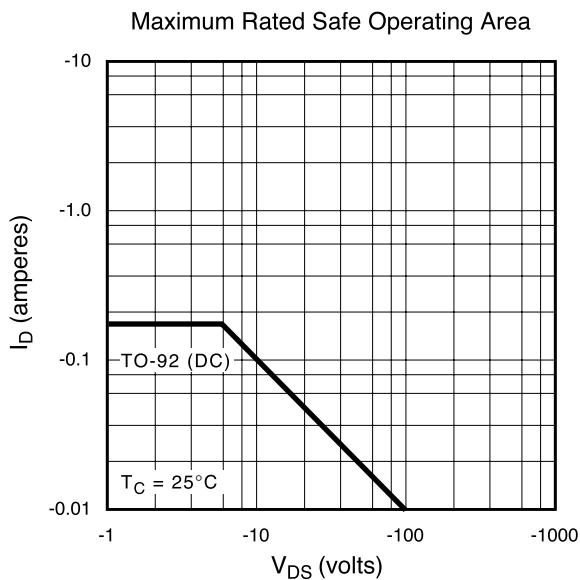
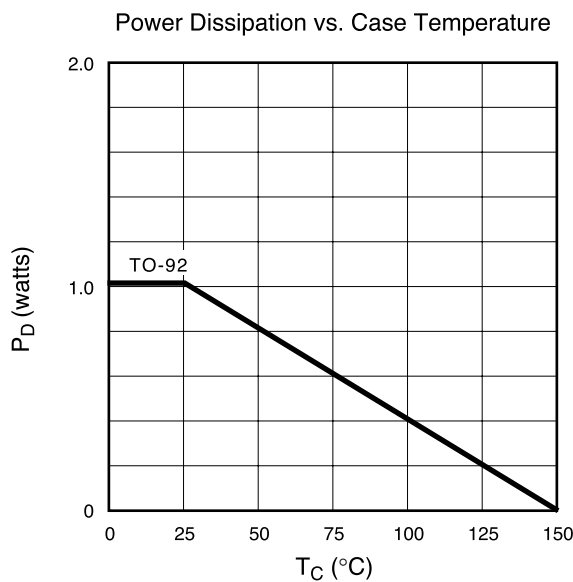
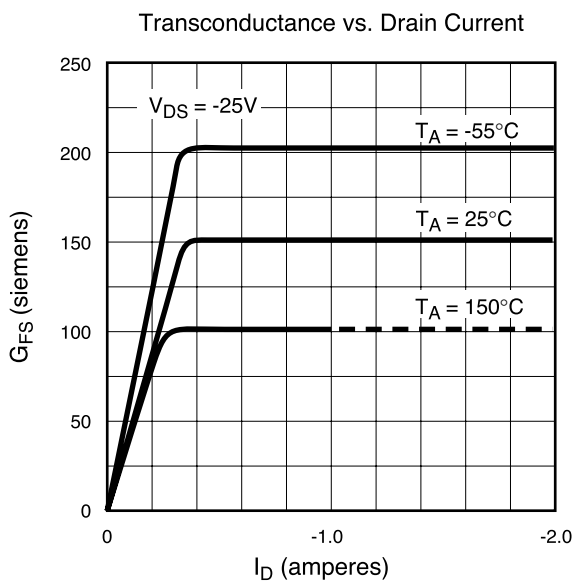
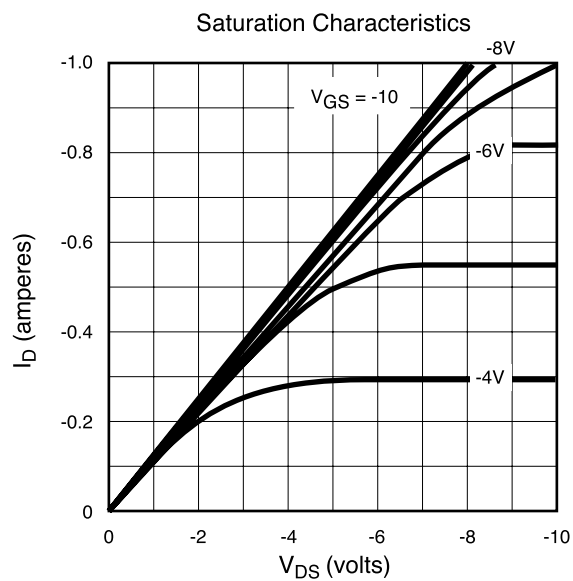
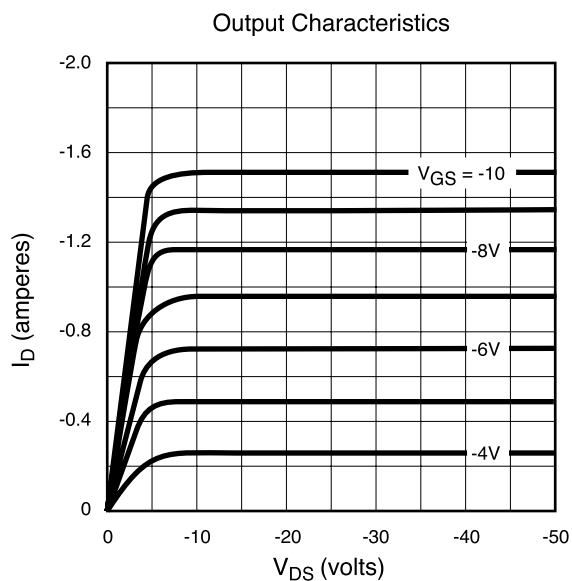
Notes:

- All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300 μs pulse, 2% duty cycle.)
- All A.C. parameters sample tested.

Switching Waveforms and Test Circuit

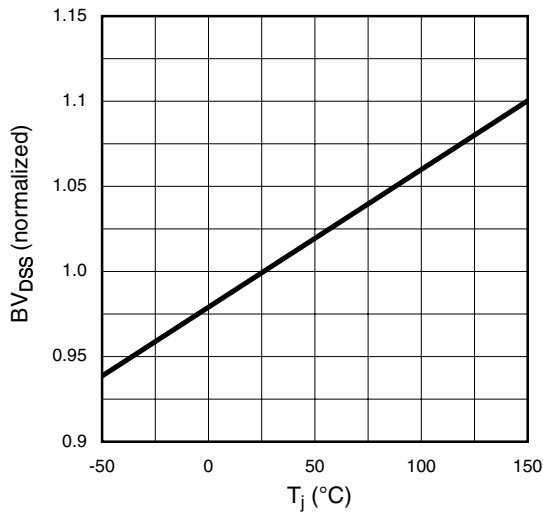


Typical Performance Curves

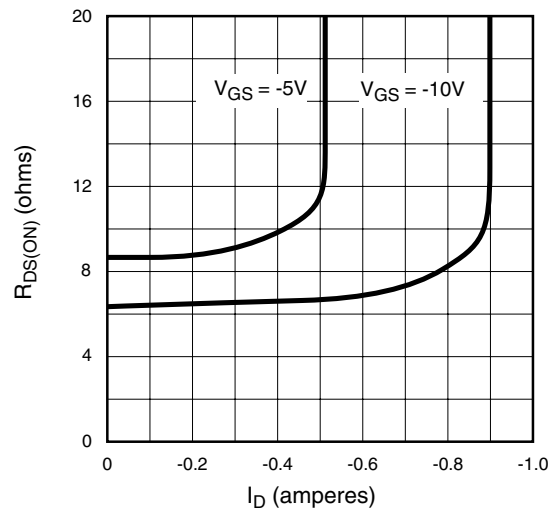


Typical Performance Curves

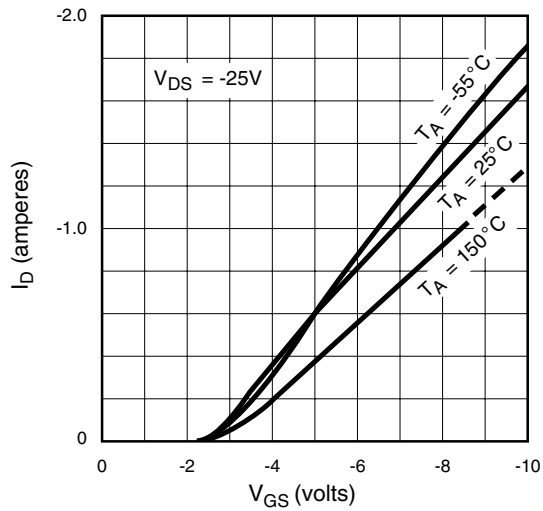
BV_{DSS} Variation with Temperature



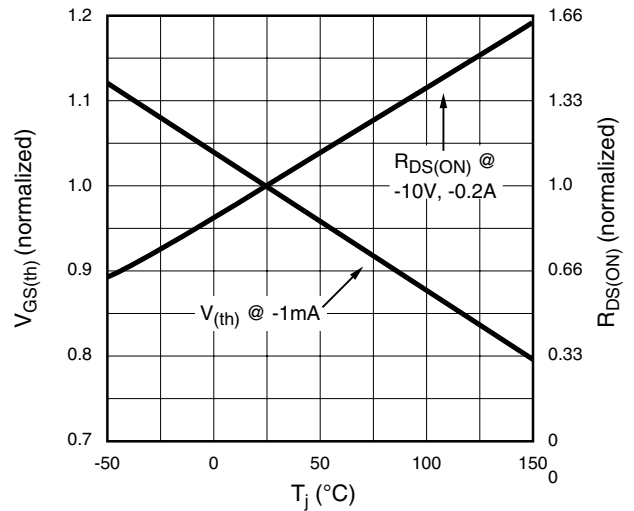
On-Resistance vs. Drain Current



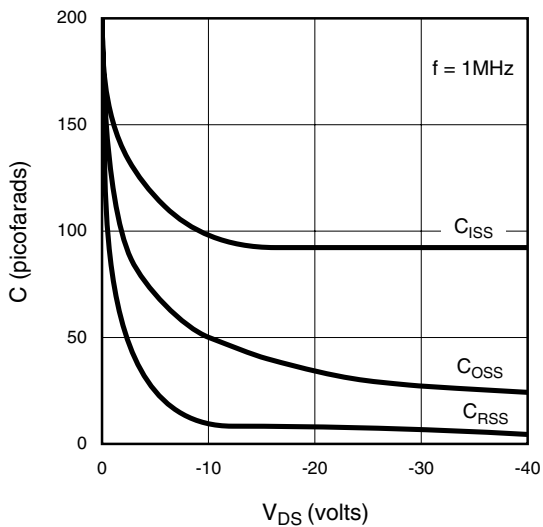
Transfer Characteristics



V_(th) and R_{DS} Variation with Temperature



Capacitance vs. Drain-to-Source Voltage



Gate Drive Dynamic Characteristics

